

Amendments to the Specification

Please replace paragraph [0017] with the following amended paragraph:

[0017] In a modified embodiment, etchant is supplied to the deposition chamber for a portion of the period of SiGe film growth; that is, in such embodiments the flow of etchant can be halted when a desired planarity is achieved. This configuration advantageously provides an increased SiGe film growth rate once the etchant flow is halted. In another modified embodiment, etchant is supplied to the deposition chamber only after a certain thickness of SiGe has been grown.